



2815

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

## Applicant:

Huili Shao  
Susan Vitkavage  
Allen Yen

Case: 1-10-31

Serial No.: 09/464,811

I hereby certify that this correspondence is being faxed to the United States Postal Service at (703) 872-9318 on November 27, 2002 and mailed first class mail in an envelope addressed to: Commissioner of Patents and Trademarks Washington, D.C. 20231 on December 2, 2002.

*MARY V. CARLTON*  
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Group Art Unit: 2815

Filed: December 17, 1999

Examiner: L. Cruz

Title: Integration of Low Dielectric Material in Semiconductor Circuit Structures

## AMENDMENT

Assistant Commissioner of Patents  
Washington, D.C. 20231

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SIR:

In response to the office action of November 1, 2002, please amend the above-identified application as follows:

**IN THE CLAIMS**

22. (Amended) A method for forming a semiconductor structure, comprising:

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depositing a first insulative layer over a semiconductor layer;  
forming a lower level of interconnect members over the first insulative layer;  
depositing a second insulative layer between and over the lower level of interconnect members;  
forming an upper level of interconnect members over the second insulative layer  
removing portions of the second insulative layer positioned between interconnect members of the lower and upper levels; and  
forming a third insulative layer in regions from which the second insulative layer is removed.